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# 2N5251 (#23338)

### Overview

### Diagrams

Electrical Rating	Symbol	Min	Typ	Max	Unit
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$			2.50	V
DC Current Gain	HFE	10.00		40.00	

Maximum Electrical Rating	Symbol	Min	Typ	Max	Unit
Breakdown Voltage, Collector-Base (Emitter Open)	$V_{BR(CBO)}$			180.00	V
Collector Current (dc)	$I_C$			90.00	A
Collector-Emitter Voltage (Base Open)	$V_{CEO}$			150.00	V
Emitter-Base Voltage (Collector Open)	$V_{EBO}$			10.00	V
Power Dissipation, Total	$P_T$			350.00	W

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